

IN THE CLAIMS:

Kindly cancel Claim 5 and amend Claims 1, 6, 8 and 11 as follows. All of the claims in the application are set forth below together with a listing of their status.

1. (Previously Amended) An electrode structure for an iontophoresis device comprising::
a backing having a substrate film having a molding portion,
an electrode layer formed passing the outer circumferential portion from the inner bottom of the molding portion,
an insulating layer formed ~~in~~ on at least the outer circumferential portion of the molding portion and also ~~in~~ on the upper portion of the electrode layer,
a conductive layer ~~formed~~ disposed in the molding portion, and
a cover member made of water-impermeable material for covering the conductive layer and the insulating layer ~~in a separable manner~~ wherein the cover member seals the insulating layer formed on the outer circumferential portion of the molding portion in a separable manner, thereby allowing the conductive layer disposed in the molding portion to be kept in a sealed state.

2. (Original) The electrode structure for the iontophoresis device according to claim 1, wherein an adhesive sheet is installed in the rear face of the substrate film of the backing.

3. (Previously Amended) The electrode structure for the iontophoresis device according to claim 1, wherein the sinking depth in the molding portion of the substrate film is in a range of 0.5 mm to 7.5 mm.

4. (Previously Amended) The electrode structure for the iontophoresis device according to

claim 1, wherein the molding angle in the molding portion of the substrate film is in a range of 5° to 70°.

5. (Cancelled)

6. (Currently Amended) The electrode structure for the iontophoresis device according to claim 5, wherein the separation mechanism between the insulating layer and the cover member is interfacial separation.

7. (Original) The electrode structure for the iontophoresis device according to claim 6, wherein the 180 degree-peel strength between the insulating layer and the cover member is in a range of 100 g to 1,500 g per 15 mm.

8. (Currently Amended) An electrode structure for an iontophoresis device comprising:
a backing having a substrate film provided with a molding portion having a dent, a flange portion formed in the outer circumferential portion of the molding portion, and a lead portion led out of the flange portion, an electrode layer formed from the inner bottom of the molding portion to the lead portion through the flange portion, and an insulating layer formed on at least the flange portion and also ~~in-on~~ the upper portion of the electrode layer;

a conductive layer ~~formed~~ disposed in the molding portion;

and a cover member made of water-impermeable material for sealing ~~the backing between the~~ insulating layer formed on the flange portion and the material itself in a separable manner to allow the conductive layer disposed in the molding portion to be kept in a sealed state.

9. (Original) The electrode structure for the iontophoresis device according to claim 8, wherein the lead portion formed in the electrode layer is so composed as to be connected with the

clip portion of a connection cord.

10. (Original) The electrode structure for the iontophoresis device according to claim 8, wherein the lead portion formed in the electrode layer has an insertion inlet for a connector.

11. (Currently Amended) A method of producing an electrode structure for an iontophoresis device comprising

- (a) a step of printing a conductive layer and an insulating layer on a substrate film,
- (b) a step of forming a molding portion in the substrate film in a manner that the insulating layer is positioned at least ~~in the~~ on an outer circumferential portion,
- (c) a step of disposing a conductive layer in the molding portion,
- (d) a step of supplying a cover member made of water-impermeable material to the substrate film and sealing between the insulating layer positioned in the outer circumferential portion and the cover member to allow the conductive layer disposed in the molding portion to be kept in a sealed state, and
- (e) a step of cutting the substrate film and the cover member in a predetermined shape.

12. (Original) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein at least the steps (b) to (e) are carried out in a continuous line.

13. (Previously Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the method further comprises a step of supplying an adhesive sheet to the rear face of the substrate film and cutting the sheet into a predetermined shape.

14. (Previously Amended) The method of producing the electrode structure for the

iontophoresis device according to claim 11, wherein the step of forming the molding portion is carried out while a convexity portion of a press die being butted to at least the electrode layer on the substrate film.

15. (Previously Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the step of forming the molding portion in the substrate film is carried out by cold processing at a temperature lower than the thermal deformation.

16. (Previously Amended) The method of producing the electrode structure for the iontophoresis device according to claim 11, wherein the step of disposing the conductive layer to the molding portion includes a step of promoting gelling of conductive gel composing the conductive layer.

17. (Original) The method of producing the electrode structure for the iontophoresis device according to claim 16, wherein the step of promoting the gelling is to promote gelling by physical cross-linking by cooling or chemical cross-linking by light or heat.